

Formula (8)

(where each of R^7 and R^8 is a C_{1-10} alkyl group, a C_{1-4} fluoroalkyl group, a hydroxy group, an allyl group, an allyloxy group, an amino group, a cyano group, a nitro group, an acyl group, an acyloxy group, a carboxy group, a group having a tertiary carbon atom, a cycloalkyl group, or a combination of any of these groups; each of n7 and n8 is an integer of 0 to 4; and T^4 is an alkylene group, a sulfonyl group, a carbonyl group, a C_{6-30} arylene group optionally having a substituent, or a combination of any of these groups).

13. The composition for forming a passivation film according to any one of claims 6 to 11, wherein

the group having a tertiary carbon atom is a tertiary butyl group.

14. The composition for forming a passivation film according to any one of claims 1 to 12, wherein

weight-average molecular weight of the polymer is from 500 to 5,000,000.

15. The composition for forming a passivation film according to any one of claims 1 to 14, further comprising:

a solvent.

16. A passivation film obtained by applying the composition for forming a passivation film as claimed in any one of claims 1 to 15 to a substrate, and baking the substrate at a temperature within a range of 100°C and 350°C, for 0.5 minutes to 180 minutes.

17. The passivation film according to claim 16, wherein

the passivation film is used as a film protecting an IC circuit formed on a wafer.

18. The passivation film according to claim 16, wherein

the passivation film is used as a film protecting an electrode formed on a rear surface of a wafer.